

Schottky Barrier Rectifier Reverse Voltage 40 to 200 Volts Forward Current 40 Amperes

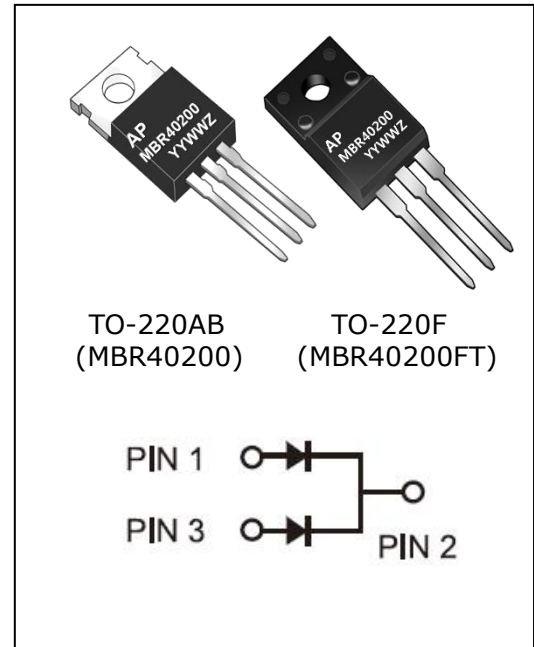
Features

- Metal silicon junction majority carrier conduction
- Guard ring for overvoltage protection
- Low power loss, high efficiency
- High current capability, low forward voltage drop
- High surge capability
- High temperature soldering guaranteed:
260°C/10 seconds at terminals
- Plastic package has Underwriters Laboratory
Flammability Classification 94V-0
- For use in low voltage, high frequency inverters,
free-wheeling, and polarity protection application

Technical Data

Case : JEDEC TO-220 molded plastic body

Terminals : Plated axial leads, solderable
per MIL-STD-750, method 2026



Maximum Ratings Characteristics

TA = 25°C unless otherwise specified. Single phase, half wave, 60HZ, resistive or inductive load. For capacitive load, derate current by 20%.

| Parameter | Symbol | MBR 4040 | MBR 4045 | MBR 4060 | MBR 4080 | MBR 40100 | MBR 40120 | MBR 40150 | MBR 40200 | Unit | |
|---|---------------------------|-------------|----------|----------|----------|-----------|-----------|-----------|-----------|------|---|
| Maximum Repetitive Peak Reverse Voltage | V_{RRM} | 40 | 45 | 60 | 80 | 100 | 120 | 150 | 200 | V | |
| Maximum RMS voltage | V_{RMS} | 28 | 31.5 | 42 | 56 | 70 | 84 | 105 | 140 | V | |
| Maximum DC Blocking Voltage | V_{DC} | 40 | 45 | 60 | 80 | 100 | 120 | 150 | 200 | V | |
| Maximum Average Forward Rectified Current 0.375" (9.5mm) lead length | $I_{F(AV)}$ | 40.0 | | | | | | | | A | |
| Peak forward surge current, 8.3ms single half sine-wave superimposed on rated load | I_{FSM} | 200.0 | | | | | | | | A | |
| Maximum instantaneous forward voltage at $1/2I_{F(AV)}$ | V_F | 0.55 | 0.75 | 0.85 | 0.90 | 0.95 | | | | | V |
| Maximum DC Reverse Current at Rated DC Blocking Voltage | $T_a = 25^\circ\text{C}$ | 0.5 | | | 0.1 | | | | | mA | |
| | $T_a = 100^\circ\text{C}$ | 50 | | | 10 | | | | | | |
| Typical Junction Capacitance ⁽¹⁾ | C_j | 300 | | | | | | | | pF | |
| Typical Thermal Resistance ⁽²⁾ | $R_{\theta JC}$ | 4 | | | | | | | | °C/W | |
| Operating and Storage Temperature Range | T_J, T_{STG} | -55 to +150 | | | | | | | | °C | |

Note

- (1) Single phase, half wave, 60HZ, resistive or inductive load. For capacitive load, derate current by 20%.
- (2) PCB mounted with 0.2X0.2"(5.0X5.0 mm) copper pad areas.



Characteristics Curves

(TA = 25°C unless otherwise specified)

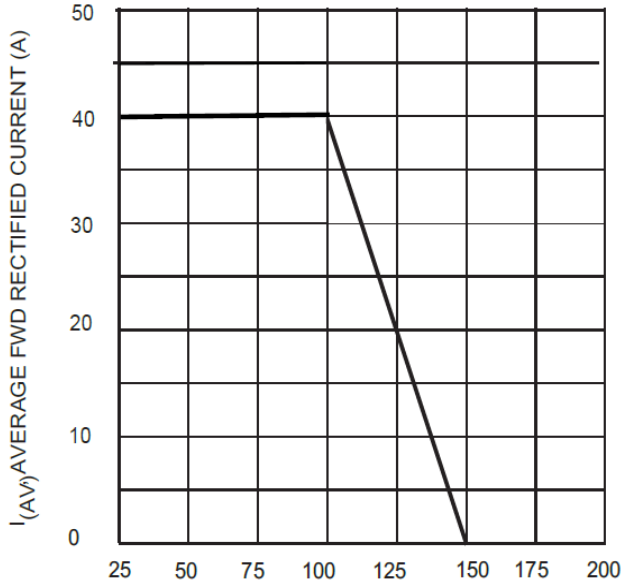


Fig. 1 Forward Derating Curve

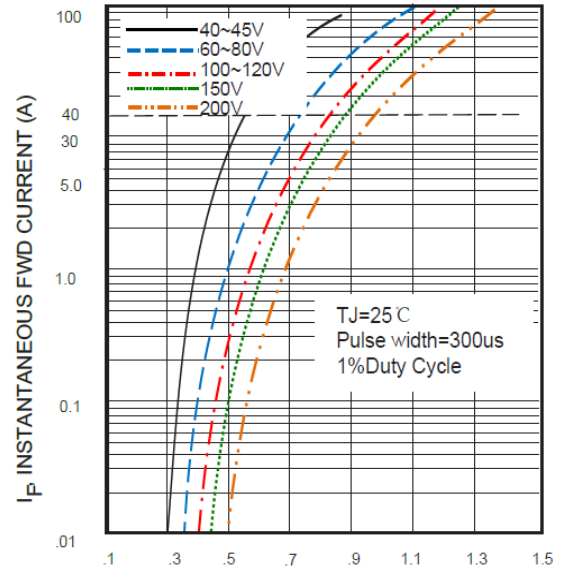


Fig. 2 Typical Forward Characteristics

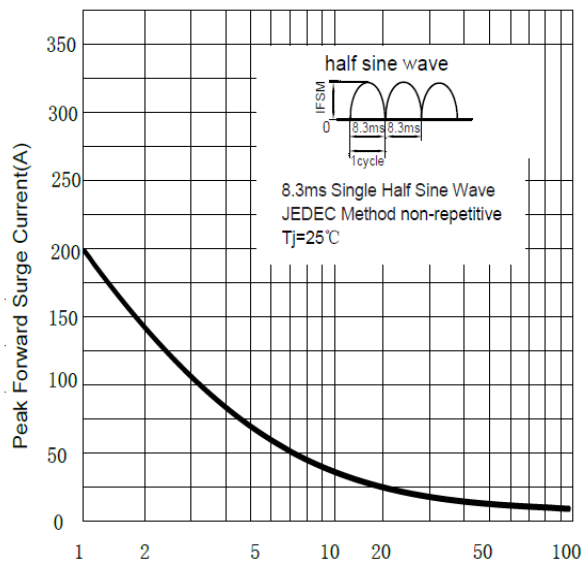


Fig. 3 Peak Forward Surge Current

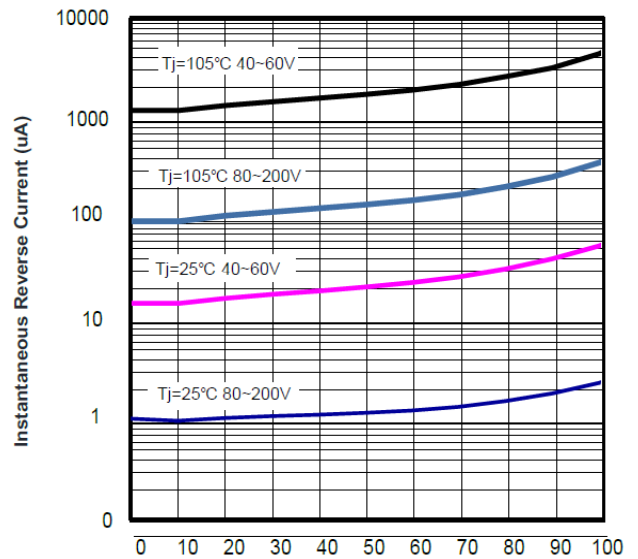


FIG.4-TYPICAL FORWARD CHARACTERISTICS

Revision History



Semi

Advanced Power Semiconductor

MBR4040(FT) THRU MBR40200(FT)

| No | Date | Contents |
|----|------------|---------------------------------|
| 0 | 2017-06-08 | Initial Brief Datasheet Release |
| | | |
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<http://www.apsemi.com>

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